

BAS21T-Q1

150mW Surface Mount Switching Diode- 250V

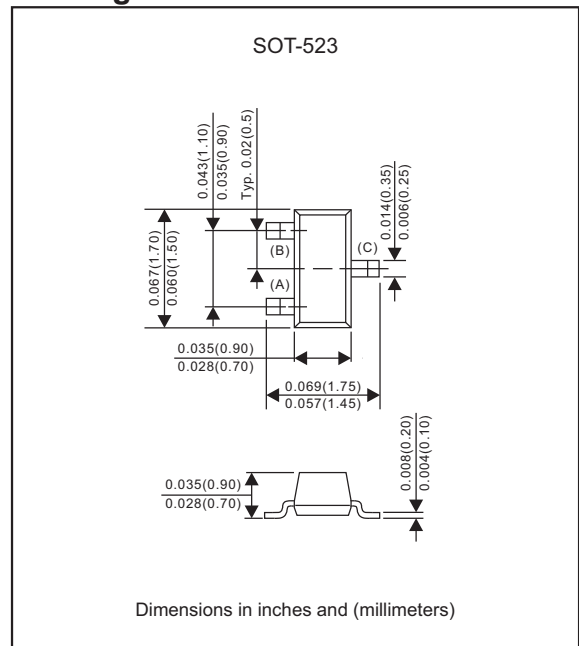
Features

- Fast Switching Speed.
- For general purpose switching application.
- High conductance.
- Silicon epitaxial planar chip
- Lead-free parts meet RoHS requirements.
- Qualified to AEC-Q101 standards for high reliability.
- Suffix "-H" indicates Halogen-free part, ex. BAS21T-Q1-H.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-523
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.003 gram

Package outline



Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	BAS21T-Q1	UNIT
Peak Repetitive Peak Reverse Voltage	V_{RRM}	250	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	400	mA
Average Rectified Output Current	I_O	200	mA
Non-Repetitive Peak Forward Surge Current @ $t = 8.3\text{ms}$	I_{FSM}	2.5	A
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise specified)

PARAMETER	CONDITION	SYMBOL	MIN.	MAX.	UNIT
Reverse Breakdown Voltage	$I_R = 100\mu\text{A}$	V_R	250		V
Forward Voltage	$I_F = 100\text{mA}$	V_F		1.0	V
	$I_F = 200\text{mA}$			1.25	
Reverse Leakage Current	$V_R = 200\text{V}$	I_R		100	nA
Total capacitance	$V_R = 0\text{V}, f = 1\text{MHz}$	C_T		5	pF
Reverse recovery time	$I_F=I_R=30\text{mA}, I_{RR}=0.1 \times I_R, R_L=100\Omega$	T_{rr}		50	ns

Rating and characteristic curves for each diode (BAS21T-Q1)

Fig.1 FORWARD CHARACTERISTICS

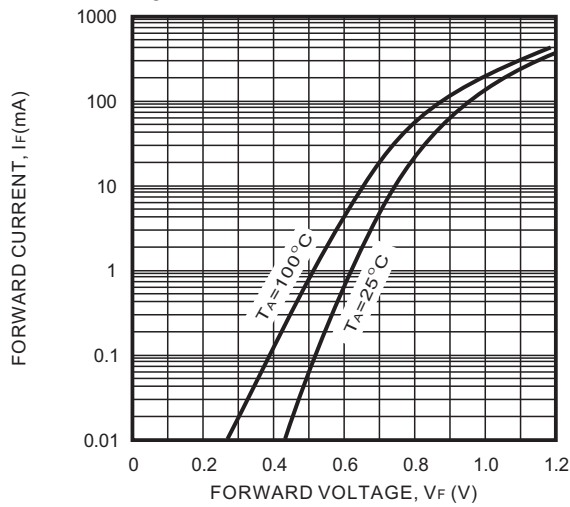


Fig.2 REVERSE CHARACTERISTICS

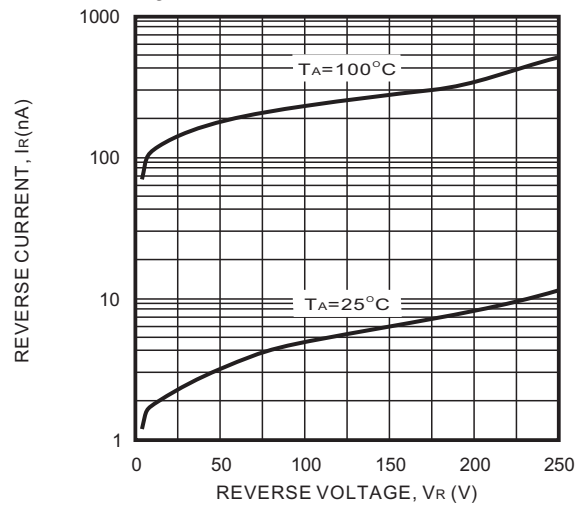


Fig.3 CAPACITANCE CHARACTERISTICS

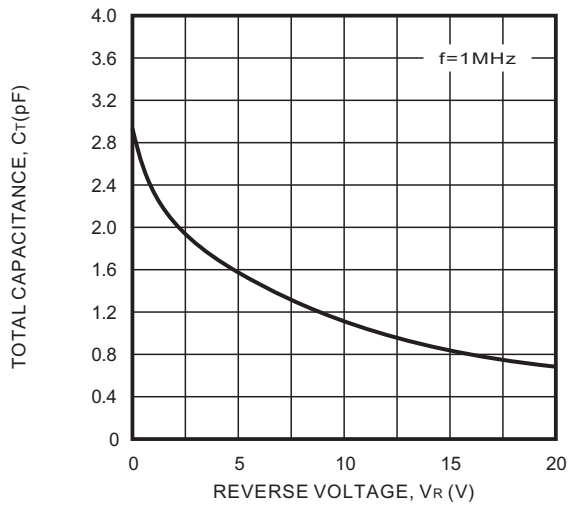
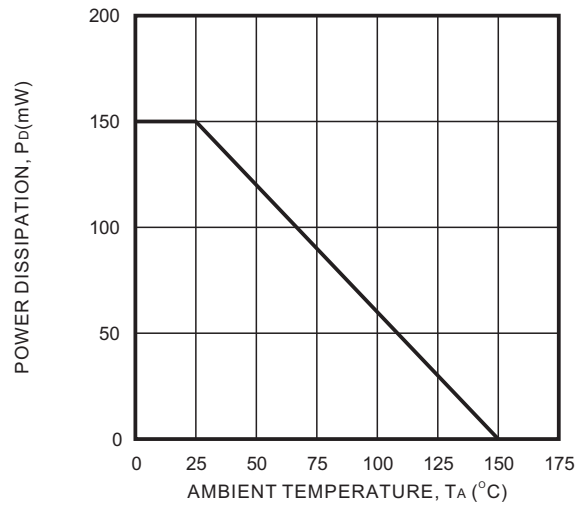
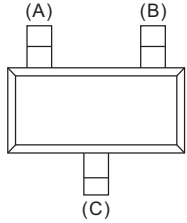
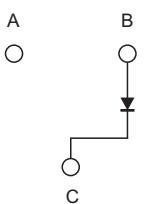


Fig.4 POWER DERATING CURVE



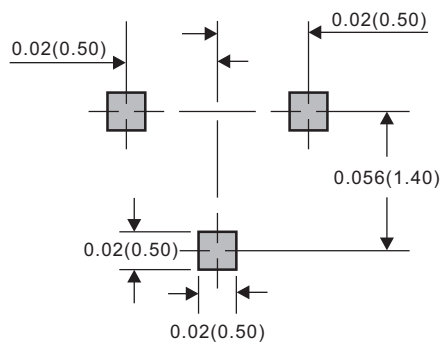
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Pinning information

Type number	Marking code	Simplified outline	Symbol
BAS21T-Q1	T3		

Suggested solder pad layout

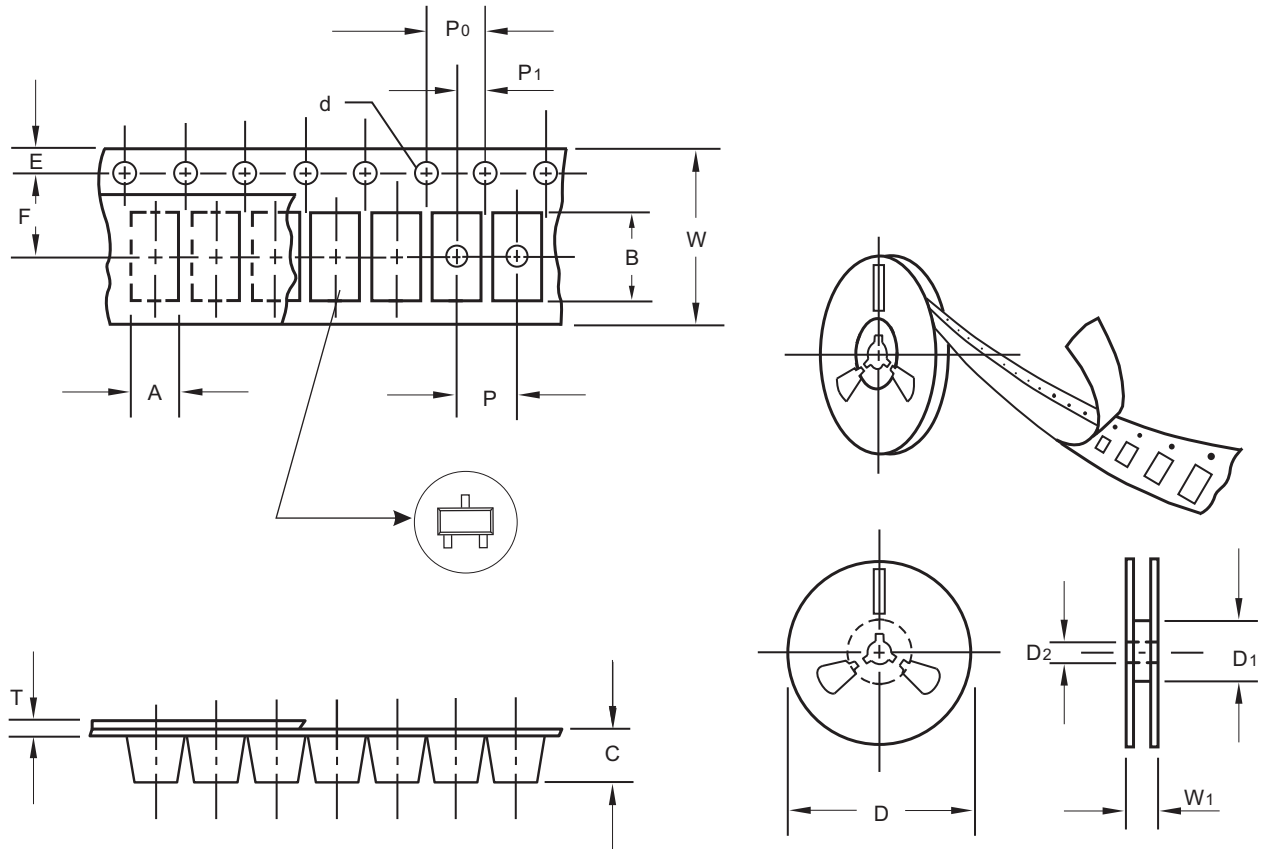
SOT-523



Dimensions in inches and (millimeters)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOT-523
Carrier width	A	0.1	1.73
Carrier length	B	0.1	1.85
Carrier depth	C	0.1	0.90
Sprocket hole	d	0.1	1.5
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	60.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

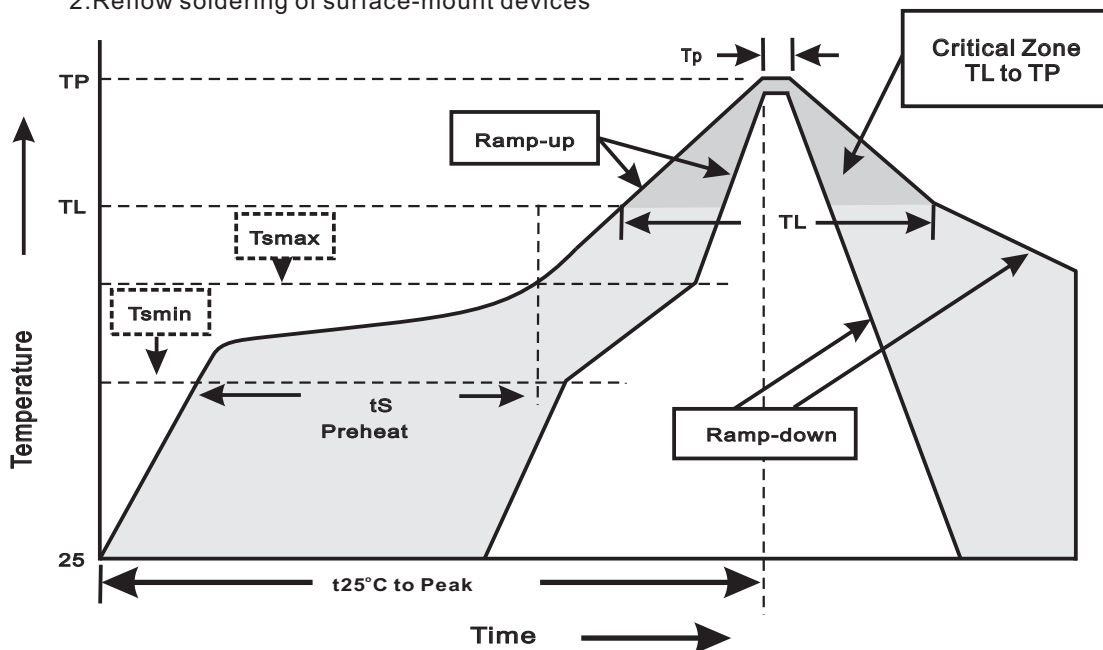
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-523	7"	3,000	4.0	30,000	183*183*123	178	382*262*387	240,000	11.6

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(TL to TP)	<3°C/sec
Preheat -Temperature Min(Tsmin) -Temperature Max(Tsmax) -Time(min to max)(ts)	150°C 200°C 60~120sec
Tsmax to TL -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(TL) -Time(tL)	217°C 60~260sec
Peak Temperature(TP)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(tp)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

BAS21T-Q1**High reliability test capabilities**

Item Test	Conditions	Reference
1. MSL Preconditioning	24hr bake@125°C+168hrs@85°C /85%RH+3xIR@260°C+1flux immersion+alcohol+DI H2O rinse	JESD22-A113
2. Operation Life	Ta=25°C, Rated Current (Io=Iomax.) Test Duration:1000hrs	MIL-STD-750E METHOD 1027.3
3. High Temperature Reverse Bias	80% Rated VR (Tj=Tjmax.) Test Duration:1000hrs	JESD22-A108
4. High Temperature Storage Life	Ta=125°C Test Duration: 1000hrs	JESD22 A-103
5. Temperature Cycle	-55°C (15min) to 150°C (15min) Test Cycles: 1000cycles	JESD22 A-104
6. Autoclave	P=2atm Ta=121°C RH=100% Test Duration:96hrs	JESD22 A-102
7. Intermittent Operational Life	Ta=25°C, On/Io Max. 2min, Off/2min, Test Cycles:15000cycles	MIL-STD-750E METHOD 1037
8. Solderability	245±5°C for 5sec	J-STD-002
9. Moisture Resistance	Ta=85°C/85% Relative humidity Test Duration:1000hrs	MIL-STD-750E METHOD 1021.2
10. Resistance To Solder Heat	260±5°C for 10sec	JESD22 B-106
11. High Temperature High Humidity Reverse Bias	Ta=85°C, 85%RH, with device reverse biased at 80% of rated breakdown voltage up to a maximum of 100V or limit of chamber Test Duration:1000hrs	JESD22-A101